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Details

Product Status	Active
Core Processor	12V1
Core Size	16-Bit
Speed	25MHz
Connectivity	CANbus, IrDA, LINbus, SCI, SPI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	40
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/s9s12g128f0vlfr

Table 2-20. Block Register Map (G2) (continued)

Global Address Register Name		Bit 7	6	5	4	3	2	1	Bit 0
0x0249 PTIS	R	PTIS7	PTIS6	PTIS5	PTIS4	PTIS3	PTIS2	PTIS1	PTIS0
	W								
0x024A DDRS	R	DDRS7	DDRS6	DDRS5	DDRS4	DDRS3	DDRS2	DDRS1	DDRS0
	W								
0x024B Reserved	R	0	0	0	0	0	0	0	0
	W								
0x024C PERS	R	PERS7	PERS6	PERS5	PERS4	PERS3	PERS2	PERS1	PERS0
	W								
0x024D PPSS	R	PPSS7	PPSS6	PPSS5	PPSS4	PPSS3	PPSS2	PPSS1	PPSS0
	W								
0x024E WOMS	R	WOMS7	WOMS6	WOMS5	WOMS4	WOMS3	WOMS2	WOMS1	WOMS0
	W								
0x024F PRR0	R	PRR0P3	PRR0P2	PRR0T31	PRR0T30	PRR0T21	PRR0T20	PRR0S1	PRR0S0
	W								
0x0250 PTM	R	0	0	0	0	PTM3	PTM2	PTM1	PTM0
	W								
0x0251 PTIM	R	0	0	0	0	PTIM3	PTIM2	PTIM1	PTIM0
	W								
0x0252 DDRM	R	0	0	0	0	DDRM3	DDRM2	DDRM1	DDRM0
	W								
0x0253 Reserved	R	0	0	0	0	0	0	0	0
	W								
0x0254 PERM	R	0	0	0	0	PERM3	PERM2	PERM1	PERM0
	W								
0x0255 PPSM	R	0	0	0	0	PPSM3	PPSM2	PPSM1	PPSM0
	W								
0x0256 WOMM	R	0	0	0	0	WOMM3	WOMM2	WOMM1	WOMM0
	W								
0x0257 PKGCR	R	APICLK7	0	0	0	0	PKGCR2	PKGCR1	PKGCR0
	W								

 = Unimplemented or Reserved

Table 2-78. PTI1AD Register Field Descriptions

Field	Description
7-0 PTI1AD	Port AD input data— A read always returns the buffered input state of the associated pin. It can be used to detect overload or short circuit conditions on output pins.

2.4.3.53 Port AD Data Direction Register (DDR0AD)

Address 0x0274 (G1, G2)

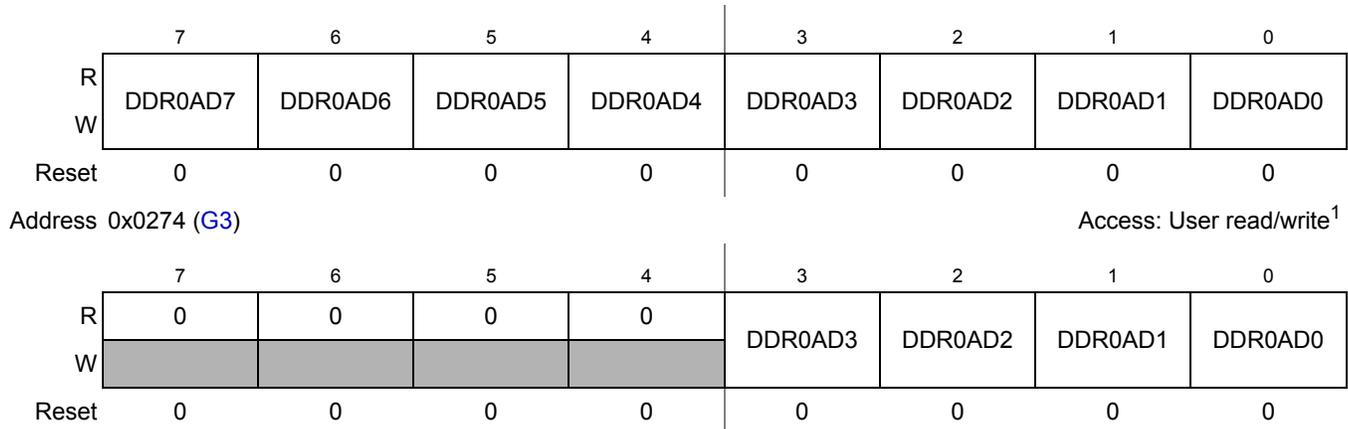
Access: User read/write¹

Figure 2-53. Port AD Data Direction Register (DDR0AD)

¹ Read: Anytime
Write: Anytime

Table 2-79. DDR0AD Register Field Descriptions

Field	Description
7-0 DDR0AD	Port AD data direction— This bit determines whether the associated pin is an input or output. 1 Associated pin configured as output 0 Associated pin configured as input

2.4.3.54 Port AD Data Direction Register (DDR1AD)

Address 0x0275

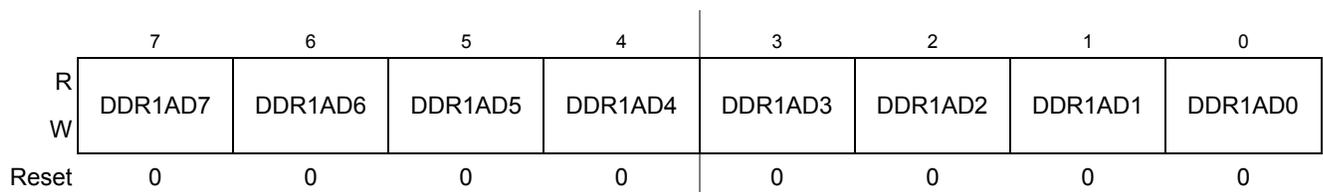
Access: User read/write¹

Figure 2-54. Port AD Data Direction Register (DDR1AD)

¹ Read: Anytime
Write: Anytime

4.6 Memory Map and Register Definition

4.6.1 Register Map

Table 4-1 shows the RVA register map.

Table 4-1. RVA Register Map

Global Address Register Name	Bit 7	6	5	4	3	2	1	Bit 0
0x0276 RVACTL	R 0	0	0	0	0	0	0	RVAON
	W							

 = Unimplemented or Reserved

4.6.2 Register Descriptions

4.6.2.1 RVA Control Register (RVACTL)

Address 0x0276

Access: User read/write¹

	7	6	5	4	3	2	1	0
R	0	0	0	0	0	0	0	RVAON
W								
Reset	0	0	0	0	0	0	0	0

Figure 4-2. RVA Control Register (RVACTL)

¹ Read: Anytime
Write: Anytime

Table 4-2. RVACTL Register Field Descriptions

Field	Description
0 RVAON	RVA On — This bit turns on the reference voltage attenuation. 0 RVA in bypass mode 1 RVA in attenuation mode

- GO_UNTIL command
- Hardware handshake protocol to increase the performance of the serial communication
- Active out of reset in special single chip mode
- Nine hardware commands using free cycles, if available, for minimal CPU intervention
- Hardware commands not requiring active BDM
- 14 firmware commands execute from the standard BDM firmware lookup table
- Software control of BDM operation during wait mode
- When secured, hardware commands are allowed to access the register space in special single chip mode, if the Flash erase tests fail.
- Family ID readable from BDM ROM at global address 0x3_FF0F in active BDM (value for devices with HCS12S core is 0xC2)
- BDM hardware commands are operational until system stop mode is entered

7.1.2 Modes of Operation

BDM is available in all operating modes but must be enabled before firmware commands are executed. Some systems may have a control bit that allows suspending the function during background debug mode.

7.1.2.1 Regular Run Modes

All of these operations refer to the part in run mode and not being secured. The BDM does not provide controls to conserve power during run mode.

- Normal modes
General operation of the BDM is available and operates the same in all normal modes.
- Special single chip mode
In special single chip mode, background operation is enabled and active out of reset. This allows programming a system with blank memory.

7.1.2.2 Secure Mode Operation

If the device is in secure mode, the operation of the BDM is reduced to a small subset of its regular run mode operation. Secure operation prevents access to Flash other than allowing erasure. For more information please see [Section 7.4.1, “Security”](#).

7.1.2.3 Low-Power Modes

The BDM can be used until stop mode is entered. When CPU is in wait mode all BDM firmware commands as well as the hardware BACKGROUND command cannot be used and are ignored. In this case the CPU can not enter BDM active mode, and only hardware read and write commands are available. Also the CPU can not enter a low power mode (stop or wait) during BDM active mode.

In stop mode the BDM clocks are stopped. When BDM clocks are disabled and stop mode is exited, the BDM clocks will restart and BDM will have a soft reset (clearing the instruction register, any command in progress and disable the ACK function). The BDM is now ready to receive a new command.

14.1 Introduction

The ADC12B12C is a 12-channel, 12-bit, multiplexed input successive approximation analog-to-digital converter. Refer to device electrical specifications for ATD accuracy.

14.1.1 Features

- 8-, 10-, or 12-bit resolution.
- Automatic return to low power after conversion sequence
- Automatic compare with interrupt for higher than or less/equal than programmable value
- Programmable sample time.
- Left/right justified result data.
- External trigger control.
- Sequence complete interrupt.
- Analog input multiplexer for 8 analog input channels.
- Special conversions for VRH, VRL, $(VRL+VRH)/2$.
- 1-to-12 conversion sequence lengths.
- Continuous conversion mode.
- Multiple channel scans.
- Configurable external trigger functionality on any AD channel or any of four additional trigger inputs. The four additional trigger inputs can be chip external or internal. Refer to device specification for availability and connectivity.
- Configurable location for channel wrap around (when converting multiple channels in a sequence).

Address	Name		Bit 7	6	5	4	3	2	1	Bit 0
0x0024	ATDDR10	R	See Section 14.3.2.12.1, "Left Justified Result Data (DJM=0)" and Section 14.3.2.12.2, "Right Justified Result Data (DJM=1)"							
		W								
0x0026	ATDDR11	R	See Section 14.3.2.12.1, "Left Justified Result Data (DJM=0)" and Section 14.3.2.12.2, "Right Justified Result Data (DJM=1)"							
		W								
0x0028 - 0x002F	Unimple- mented	R	0	0	0	0	0	0	0	0
		W								

 = Unimplemented or Reserved

Figure 14-2. ADC12B12C Register Summary (Sheet 3 of 3)

14.3.2.12.2 Right Justified Result Data (DJM=1)

Module Base +

0x0010 = ATDDR0, 0x0012 = ATDDR1, 0x0014 = ATDDR2, 0x0016 = ATDDR3

0x0018 = ATDDR4, 0x001A = ATDDR5, 0x001C = ATDDR6, 0x001E = ATDDR7

0x0020 = ATDDR8, 0x0022 = ATDDR9, 0x0024 = ATDDR10, 0x0026 = ATDDR11

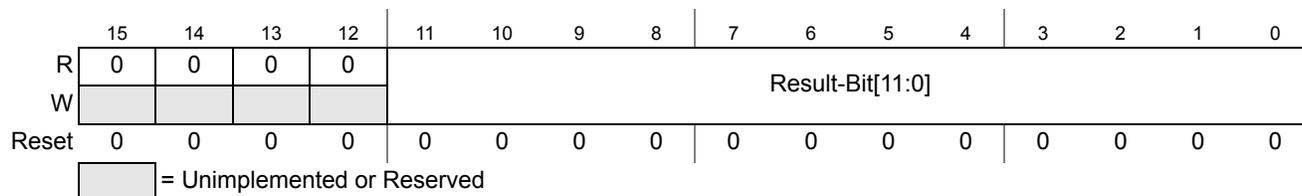


Figure 14-15. Right justified ATD conversion result register (ATDDR n)

Table 14-22 shows how depending on the A/D resolution the conversion result is transferred to the ATD result registers for right justified data. Compare is always done using all 12 bits of both the conversion result and the compare value in ATDDR n .

Table 14-22. Conversion result mapping to ATDDR n

A/D resolution	DJM	conversion result mapping to ATDDR n
8-bit data	1	Result-Bit[11:8]=0000, Result-Bit[7:0] = conversion result
10-bit data	1	Result-Bit[11:10]=00, Result-Bit[9:0] = conversion result
12-bit data	1	Result-Bit[11:0] = result

18.3.2.15 MSCAN Receive Error Counter (CANRXERR)

This register reflects the status of the MSCAN receive error counter.

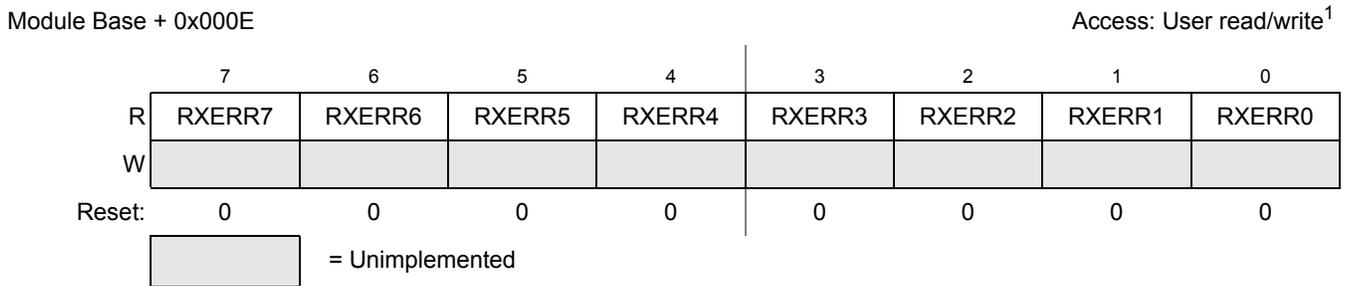


Figure 18-18. MSCAN Receive Error Counter (CANRXERR)

¹ Read: Only when in sleep mode (SLPRQ = 1 and SLPK = 1) or initialization mode (INITRQ = 1 and INITAK = 1)
 Write: Unimplemented

NOTE

Reading this register when in any other mode other than sleep or initialization mode may return an incorrect value. For MCUs with dual CPUs, this may result in a CPU fault condition.

18.3.2.16 MSCAN Transmit Error Counter (CANTXERR)

This register reflects the status of the MSCAN transmit error counter.

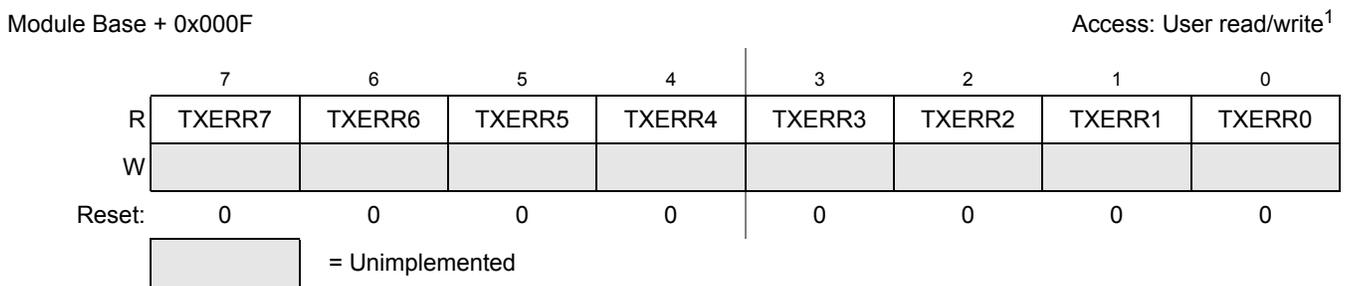


Figure 18-19. MSCAN Transmit Error Counter (CANTXERR)

¹ Read: Only when in sleep mode (SLPRQ = 1 and SLPK = 1) or initialization mode (INITRQ = 1 and INITAK = 1)
 Write: Unimplemented

NOTE

Reading this register when in any other mode other than sleep or initialization mode, may return an incorrect value. For MCUs with dual CPUs, this may result in a CPU fault condition.

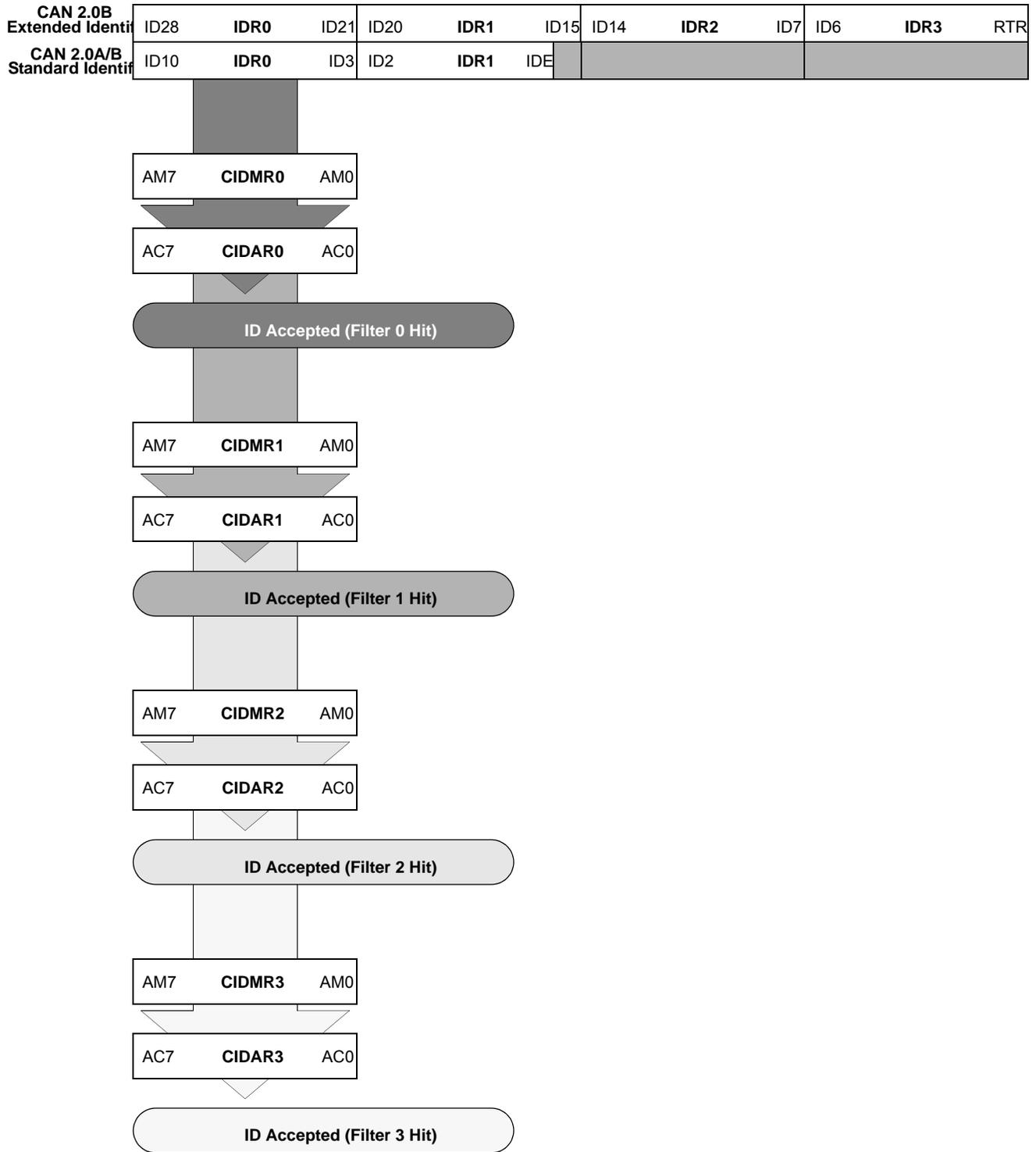


Figure 18-42. 8-bit Maskable Identifier Acceptance Filters

Table 20-2. SCIBDH and SCIBDL Field Descriptions

Field	Description
7 IREN	Infrared Enable Bit — This bit enables/disables the infrared modulation/demodulation submodule. 0 IR disabled 1 IR enabled
6:5 TNP[1:0]	Transmitter Narrow Pulse Bits — These bits enable whether the SCI transmits a 1/16, 3/16, 1/32 or 1/4 narrow pulse. See Table 20-3.
4:0 7:0 SBR[12:0]	SCI Baud Rate Bits — The baud rate for the SCI is determined by the bits in this register. The baud rate is calculated two different ways depending on the state of the IREN bit. The formulas for calculating the baud rate are: When IREN = 0 then, SCI baud rate = SCI bus clock / (16 x SBR[12:0]) When IREN = 1 then, SCI baud rate = SCI bus clock / (32 x SBR[12:1]) Note: The baud rate generator is disabled after reset and not started until the TE bit or the RE bit is set for the first time. The baud rate generator is disabled when (SBR[12:0] = 0 and IREN = 0) or (SBR[12:1] = 0 and IREN = 1). Note: Writing to SCIBDH has no effect without writing to SCIBDL, because writing to SCIBDH puts the data in a temporary location until SCIBDL is written to.

Table 20-3. IRSCI Transmit Pulse Width

TNP[1:0]	Narrow Pulse Width
11	1/4
10	1/32
01	1/16
00	3/16

20.3.2.2 SCI Control Register 1 (SCICR1)

Module Base + 0x0002

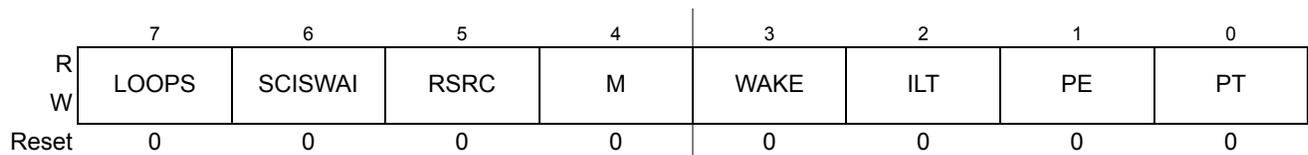


Figure 20-5. SCI Control Register 1 (SCICR1)

Read: Anytime, if AMAP = 0.

Write: Anytime, if AMAP = 0.

NOTE

This register is only visible in the memory map if AMAP = 0 (reset condition).

Table 22-16. PTPSR Field Descriptions

Field	Description
7:0 PTPS[7:0]	Precision Timer Prescaler Select Bits — These eight bits specify the division rate of the main Timer prescaler. These are effective only when the PRNT bit of TSCR1 is set to 1. Table 22-17 shows some selection examples in this case. The newly selected prescale factor will not take effect until the next synchronized edge where all prescale counter stages equal zero.

The Prescaler can be calculated as follows depending on logical value of the PTPS[7:0] and PRNT bit:

$$\text{PRNT} = 1 : \text{Prescaler} = \text{PTPS}[7:0] + 1$$

Table 22-17. Precision Timer Prescaler Selection Examples when PRNT = 1

PTPS7	PTPS6	PTPS5	PTPS4	PTPS3	PTPS2	PTPS1	PTPS0	Prescale Factor
0	0	0	0	0	0	0	0	1
0	0	0	0	0	0	0	1	2
0	0	0	0	0	0	1	0	3
0	0	0	0	0	0	1	1	4
-	-	-	-	-	-	-	-	-
-	-	-	-	-	-	-	-	-
-	-	-	-	-	-	-	-	-
0	0	0	1	0	0	1	1	20
0	0	0	1	0	1	0	0	21
0	0	0	1	0	1	0	1	22
-	-	-	-	-	-	-	-	-
-	-	-	-	-	-	-	-	-
-	-	-	-	-	-	-	-	-
1	1	1	1	1	1	0	0	253
1	1	1	1	1	1	0	1	254
1	1	1	1	1	1	1	0	255
1	1	1	1	1	1	1	1	256

22.4 Functional Description

This section provides a complete functional description of the timer TIM16B6CV3 block. Please refer to the detailed timer block diagram in [Figure 22-22](#) as necessary.

Table 23-4. OC7M Field Descriptions

Field	Description
7:0 OC7M[7:0]	<p>Output Compare 7 Mask — A channel 7 event, which can be a counter overflow when TTOV[7] is set or a successful output compare on channel 7, overrides any channel 6:0 compares. For each OC7M bit that is set, the output compare action reflects the corresponding OC7D bit.</p> <p>0 The corresponding OC7Dx bit in the output compare 7 data register will not be transferred to the timer port on a channel 7 event, even if the corresponding pin is setup for output compare.</p> <p>1 The corresponding OC7Dx bit in the output compare 7 data register will be transferred to the timer port on a channel 7 event.</p> <p>Note: The corresponding channel must also be setup for output compare (IOSx = 1 and OCPDx = 0) for data to be transferred from the output compare 7 data register to the timer port.</p>

23.3.2.4 Output Compare 7 Data Register (OC7D)

1

Module Base + 0x0003

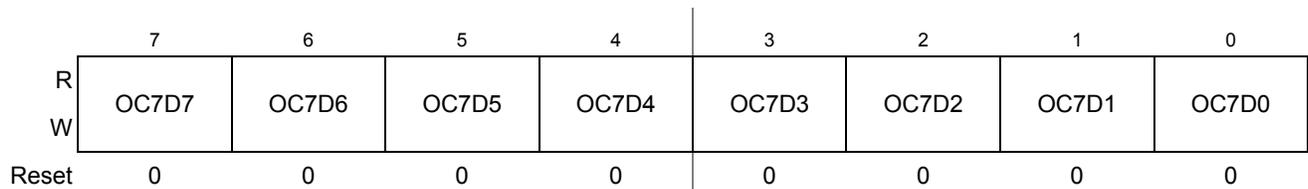


Figure 23-9. Output Compare 7 Data Register (OC7D)

Read: Anytime

Write: Anytime

Table 23-5. OC7D Field Descriptions

Field	Description
7:0 OC7D[7:0]	<p>Output Compare 7 Data — A channel 7 event, which can be a counter overflow when TTOV[7] is set or a successful output compare on channel 7, can cause bits in the output compare 7 data register to transfer to the timer port data register depending on the output compare 7 mask register.</p>

23.3.2.5 Timer Count Register (TCNT)

Module Base + 0x0004

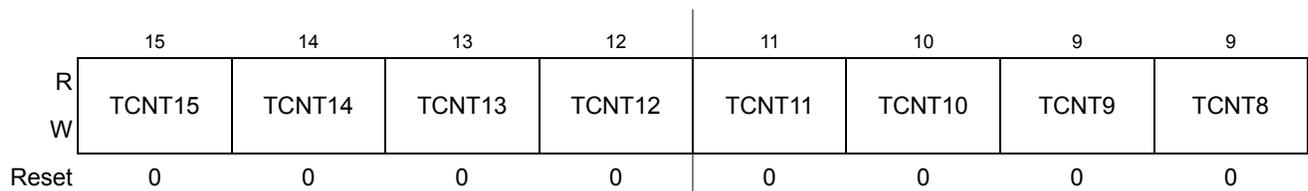


Figure 23-10. Timer Count Register High (TCNTH)

23.3.2.15 16-Bit Pulse Accumulator Control Register (PACTL)

Module Base + 0x0020

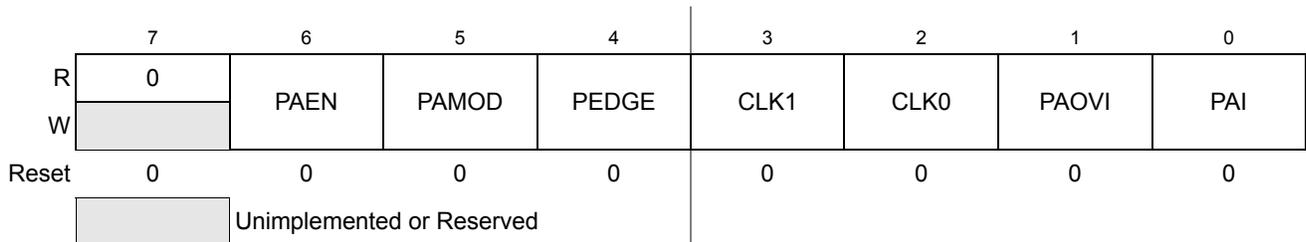


Figure 23-24. 16-Bit Pulse Accumulator Control Register (PACTL)

Read: Any time

Write: Any time

When PAEN is set, the Pulse Accumulator counter is enabled. The Pulse Accumulator counter shares the input pin with IOC7.

Table 23-18. PACTL Field Descriptions

Field	Description
6 PAEN	Pulse Accumulator System Enable — PAEN is independent from TEN. With timer disabled, the pulse accumulator can function unless pulse accumulator is disabled. 0 16-Bit Pulse Accumulator system disabled. 1 Pulse Accumulator system enabled.
5 PAMOD	Pulse Accumulator Mode — This bit is active only when the Pulse Accumulator is enabled (PAEN = 1). See Table 23-19 . 0 Event counter mode. 1 Gated time accumulation mode.
4 PEDGE	Pulse Accumulator Edge Control — This bit is active only when the Pulse Accumulator is enabled (PAEN = 1). For PAMOD bit = 0 (event counter mode). See Table 23-19 . 0 Falling edges on IOC7 pin cause the count to be increased. 1 Rising edges on IOC7 pin cause the count to be increased. For PAMOD bit = 1 (gated time accumulation mode). 0 IOC7 input pin high enables M (Bus clock) divided by 64 clock to Pulse Accumulator and the trailing falling edge on IOC7 sets the PAIF flag. 1 IOC7 input pin low enables M (Bus clock) divided by 64 clock to Pulse Accumulator and the trailing rising edge on IOC7 sets the PAIF flag.
3:2 CLK[1:0]	Clock Select Bits — Refer to Table 23-20 .
1 PAOVI	Pulse Accumulator Overflow Interrupt Enable 0 Interrupt inhibited. 1 Interrupt requested if PAOVF is set.
0 PAI	Pulse Accumulator Input Interrupt Enable 0 Interrupt inhibited. 1 Interrupt requested if PAIF is set.

Table 24-36. Read Once Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters
101	Read Once word 3 value

Upon clearing CCIF to launch the Read Once command, a Read Once phrase is fetched and stored in the FCCOB indexed register. The CCIF flag will set after the Read Once operation has completed. Valid phrase index values for the Read Once command range from 0x0000 to 0x0007. During execution of the Read Once command, any attempt to read addresses within P-Flash block will return invalid data.

Table 24-37. Read Once Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 001 at command launch
		Set if command not available in current mode (see Table 24-25)
		Set if an invalid phrase index is supplied
	FPVIOL	None
	MGSTAT1	Set if any errors have been encountered during the read
	MGSTAT0	Set if any non-correctable errors have been encountered during the read

24.4.6.5 Program P-Flash Command

The Program P-Flash operation will program a previously erased phrase in the P-Flash memory using an embedded algorithm.

CAUTION

A P-Flash phrase must be in the erased state before being programmed. Cumulative programming of bits within a Flash phrase is not allowed.

Table 24-38. Program P-Flash Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x06	Global address [17:16] to identify P-Flash block
001	Global address [15:0] of phrase location to be programmed ¹	
010	Word 0 program value	
011	Word 1 program value	
100	Word 2 program value	
101	Word 3 program value	

¹ Global address [2:0] must be 000

Upon clearing CCIF to launch the Program P-Flash command, the Memory Controller will program the data words to the supplied global address and will then proceed to verify the data words read back as expected. The CCIF flag will set after the Program P-Flash operation has completed.

NOTE

User margin levels can be used to check that Flash memory contents have adequate margin for normal level read operations. If unexpected results are encountered when checking Flash memory contents at user margin levels, a potential loss of information has been detected.

24.4.6.13 Set Field Margin Level Command

The Set Field Margin Level command, valid in special modes only, causes the Memory Controller to set the margin level specified for future read operations of the P-Flash or EEPROM block.

Upon clearing CCIF to launch the Set Field Margin Level command, the Memory Controller will set the **Table 24-55. Set Field Margin Level Command FCCOB Requirements**

CCOBIX[2:0]	FCCOB Parameters	
000	0x0E	Flash block selection code [1:0]. See Table 24-32
001	Margin level setting.	

field margin level for the targeted block and then set the CCIF flag.

NOTE

When the EEPROM block is targeted, the EEPROM field margin levels are applied only to the EEPROM reads. However, when the P-Flash block is targeted, the P-Flash field margin levels are applied to both P-Flash and EEPROM reads. It is not possible to apply field margin levels to the P-Flash block only.

Valid margin level settings for the Set Field Margin Level command are defined in [Table 24-56](#).

Table 24-56. Valid Set Field Margin Level Settings

CCOB (CCOBIX=001)	Level Description
0x0000	Return to Normal Level
0x0001	User Margin-1 Level ¹
0x0002	User Margin-0 Level ²
0x0003	Field Margin-1 Level ¹
0x0004	Field Margin-0 Level ²

¹ Read margin to the erased state

² Read margin to the programmed state

Table 25-61. Erase Verify EEPROM Section Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 010 at command launch
		Set if command not available in current mode (see Table 25-27)
		Set if an invalid global address [17:0] is supplied
		Set if a misaligned word address is supplied (global address [0] != 0)
		Set if the requested section breaches the end of the EEPROM block
	FPVIOL	None
	MGSTAT1	Set if any errors have been encountered during the read or if blank check failed.
MGSTAT0	Set if any non-correctable errors have been encountered during the read or if blank check failed.	

25.4.6.15 Program EEPROM Command

The Program EEPROM operation programs one to four previously erased words in the EEPROM block. The Program EEPROM operation will confirm that the targeted location(s) were successfully programmed upon completion.

CAUTION

A Flash word must be in the erased state before being programmed. Cumulative programming of bits within a Flash word is not allowed.

Table 25-62. Program EEPROM Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x11	Global address [17:16] to identify the EEPROM block
001	Global address [15:0] of word to be programmed	
010	Word 0 program value	
011	Word 1 program value, if desired	
100	Word 2 program value, if desired	
101	Word 3 program value, if desired	

Upon clearing CCIF to launch the Program EEPROM command, the user-supplied words will be transferred to the Memory Controller and be programmed if the area is unprotected. The CCOBIX index value at Program EEPROM command launch determines how many words will be programmed in the EEPROM block. The CCIF flag is set when the operation has completed.

It is possible to read from P-Flash memory while some commands are executing on EEPROM memory. It is not possible to read from EEPROM memory while a command is executing on P-Flash memory. Simultaneous P-Flash and EEPROM operations are discussed in [Section 26.4.5](#).

Both P-Flash and EEPROM memories are implemented with Error Correction Codes (ECC) that can resolve single bit faults and detect double bit faults. For P-Flash memory, the ECC implementation requires that programming be done on an aligned 8 byte basis (a Flash phrase). Since P-Flash memory is always read by half-phrase, only one single bit fault in an aligned 4 byte half-phrase containing the byte or word accessed will be corrected.

26.1.1 Glossary

Command Write Sequence — An MCU instruction sequence to execute built-in algorithms (including program and erase) on the Flash memory.

EEPROM Memory — The EEPROM memory constitutes the nonvolatile memory store for data.

EEPROM Sector — The EEPROM sector is the smallest portion of the EEPROM memory that can be erased. The EEPROM sector consists of 4 bytes.

NVM Command Mode — An NVM mode using the CPU to setup the FCCOB register to pass parameters required for Flash command execution.

Phrase — An aligned group of four 16-bit words within the P-Flash memory. Each phrase includes two sets of aligned double words with each set including 7 ECC bits for single bit fault correction and double bit fault detection within each double word.

P-Flash Memory — The P-Flash memory constitutes the main nonvolatile memory store for applications.

P-Flash Sector — The P-Flash sector is the smallest portion of the P-Flash memory that can be erased. Each P-Flash sector contains 512 bytes.

Program IFR — Nonvolatile information register located in the P-Flash block that contains the Version ID, and the Program Once field.

26.1.2 Features

26.1.2.1 P-Flash Features

- 48 Kbytes of P-Flash memory composed of one 48 Kbyte Flash block divided into 96 sectors of 512 bytes
- Single bit fault correction and double bit fault detection within a 32-bit double word during read operations
- Automated program and erase algorithm with verify and generation of ECC parity bits

Offset Module Base + 0x000E

	7	6	5	4	3	2	1	0
R	0	0	0	0	0	0	0	0
W								
Reset	0	0	0	0	0	0	0	0
	= Unimplemented or Reserved							

Figure 30-20. Flash Reserved3 Register (FRSV3)

All bits in the FRSV3 register read 0 and are not writable.

30.3.2.15 Flash Reserved4 Register (FRSV4)

This Flash register is reserved for factory testing.

Offset Module Base + 0x000F

	7	6	5	4	3	2	1	0
R	0	0	0	0	0	0	0	0
W								
Reset	0	0	0	0	0	0	0	0
	= Unimplemented or Reserved							

Figure 30-21. Flash Reserved4 Register (FRSV4)

All bits in the FRSV4 register read 0 and are not writable.

30.3.2.16 Flash Option Register (FOPT)

The FOPT register is the Flash option register.

Offset Module Base + 0x0010

	7	6	5	4	3	2	1	0
R	NV[7:0]							
W								
Reset	F ¹	F ¹	F ¹	F ¹	F ¹	F ¹	F ¹	F ¹
	= Unimplemented or Reserved							

Figure 30-22. Flash Option Register (FOPT)

¹ Loaded from IFR Flash configuration field, during reset sequence.

All bits in the FOPT register are readable but are not writable.

During the reset sequence, the FOPT register is loaded from the Flash nonvolatile byte in the Flash configuration field at global address 0x3_FF0E located in P-Flash memory (see [Table 30-4](#)) as indicated by reset condition F in [Figure 30-22](#). If a double bit fault is detected while reading the P-Flash phrase containing the Flash nonvolatile byte during the reset sequence, all bits in the FOPT register will be set.

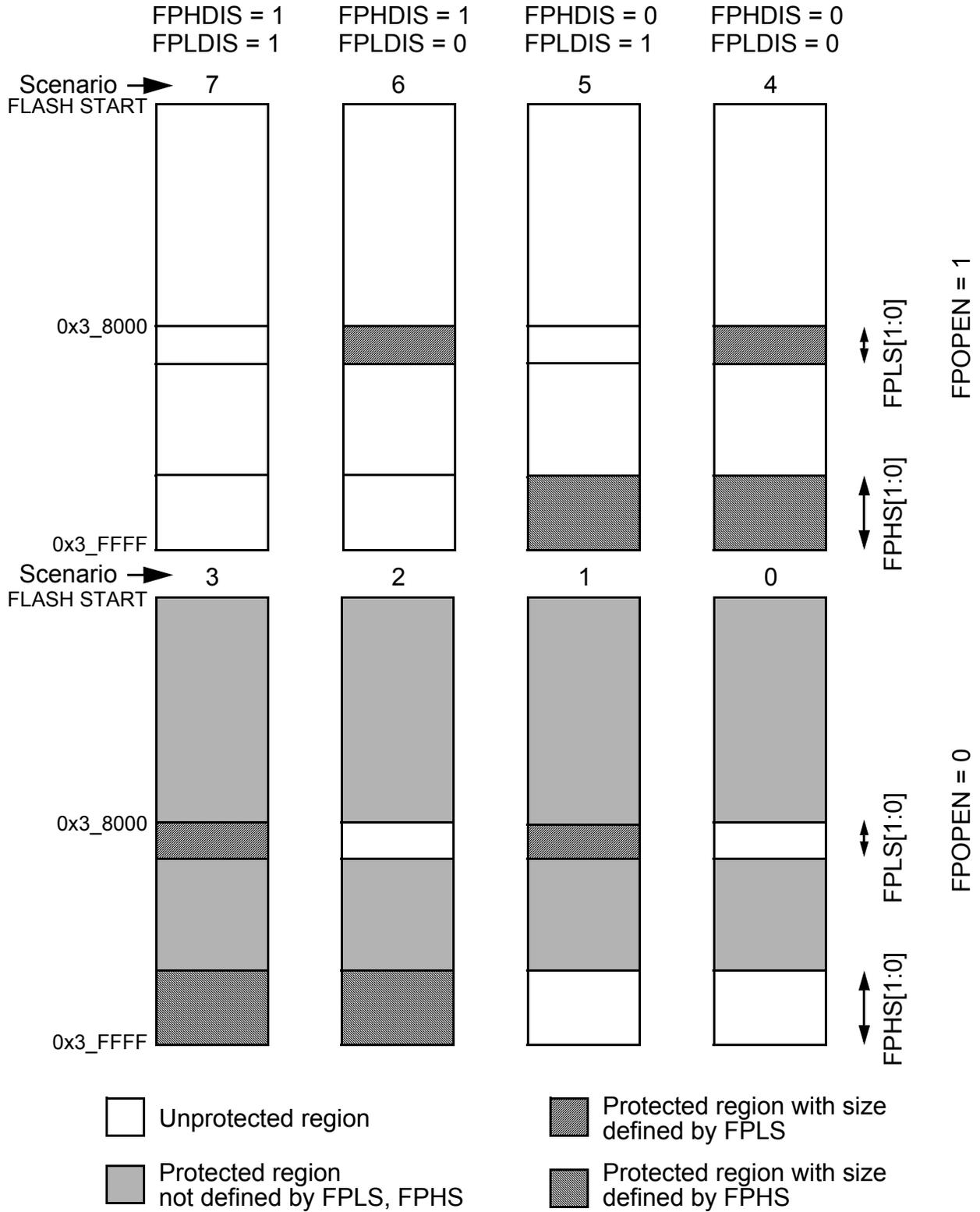


Figure 31-14. P-Flash Protection Scenarios

A.1.8 Power Dissipation and Thermal Characteristics

Power dissipation and thermal characteristics are closely related. The user must assure that the maximum operating junction temperature is not exceeded. The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \cdot \Theta_{JA})$$

T_J = Junction Temperature, [°C]

T_A = Ambient Temperature, [°C]

P_D = Total Chip Power Dissipation, [W]

Θ_{JA} = Package Thermal Resistance, [°C/W]

The total power dissipation can be calculated from:

$$P_D = P_{INT} + P_{IO}$$

P_{INT} = Chip Internal Power Dissipation, [W]

$$P_{IO} = \sum_i R_{DSON} \cdot I_{IO_i}^2$$

P_{IO} is the sum of all output currents on I/O ports associated with V_{DDX} , whereby

$$R_{DSON} = \frac{V_{OL}}{I_{OL}}; \text{for outputs driven low}$$

$$R_{DSON} = \frac{V_{DD35} - V_{OH}}{I_{OH}}; \text{for outputs driven high}$$

$$P_{INT} = I_{DDR} \cdot V_{DDR} + I_{DDA} \cdot V_{DDA}$$